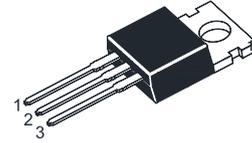


FEATURES

- High voltage, high speed switching
- High reliability

TO-220



1.Base 2.Collector 3.Emitter

GK xxx
13009

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Rating ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BV_{CBO}	700	V
Collector-Emitter Voltage	BV_{CEO}	410	V
Emitter-Base Voltage	BV_{EBO}	9	V
Collector Current	I_C	12	A
Collector Current pulse	I_{CM}	24	A
Base Current	I_B	6	A
Base Current pulse	I_{BM}	12	A
Power Dissipation	P_D	$T_a=25^\circ\text{C}$	W
		$T_C=25^\circ\text{C}$	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ\text{C}$

Note: 1. Pulse Test: Pulse Width = 5ms, Duty Cycle $\leq 10\%$

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	BV_{CBO}	$I_C = 1mA, I_E = 0$	700			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = 5mA, I_B = 0$	410			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = 0.1mA, I_C = 0$	9			V
Collector cut-off current	I_{CBO}	$V_{CB} = 700V, I_E = 0$			1	mA
Emitter cut-off current	I_{EBO}	$V_{EB} = 9V, I_C = 0$			1	mA
DC current gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 3A$	10		35	
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 2mA$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5A, I_B = 1A$ $I_C = 8A, I_B = 1.6A$ $I_C = 12A, I_B = 3A$			1.0 1.5 3	V
Base-emitter on voltage	$V_{BE(sat)}$	$I_C = 5A, I_B = 1A$ $I_C = 8A, I_B = 1.6A$			1.2 1.6	V
Transition frequency	f_T	$I_C = 0.5A, V_{CE} = 10V,$ $f = 1MHz$	4			MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0$ $f = 0.1MHz$		180		pF
Delay Time	t_d	$V_C = 125V, I_C = 8A,$ $I_{B1} = I_{B2} = 1.6A$ $t_p = 25\mu s, Duty \leq 1\%$			0.1	μs
Rise Time	t_R				1	μs
Fall Time	t_F				0.7	μs
Switching Time	t_s	$I_C = 500mA$			0.7	μs

*Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance Junction to Ambient	θ_{JA}	54	$^{\circ}C/W$
Thermal Resistance Junction to Case	θ_{JC}	4	$^{\circ}C/W$

RATING AND CHARACTERISTIC CURVES

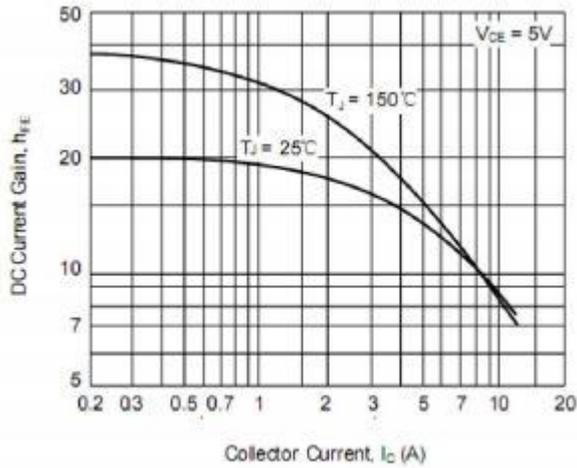


Figure 1. DC current Gain

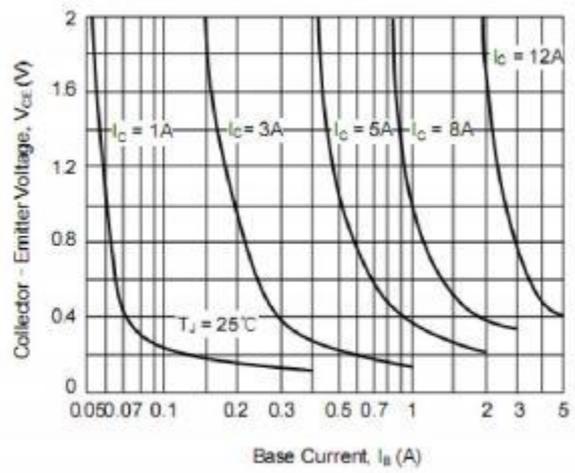


Figure 2. Collector Saturation Region

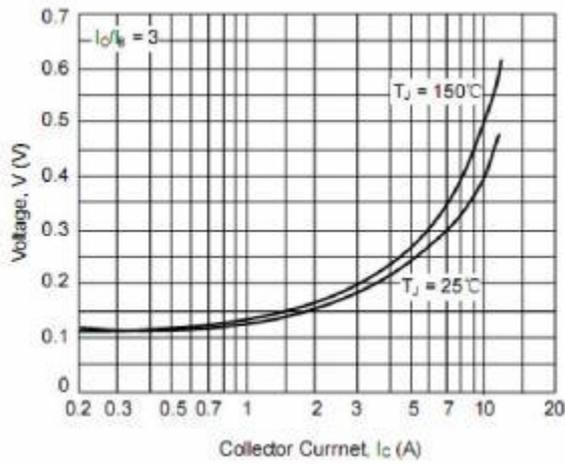


Figure 3. Collector Saturation Voltage

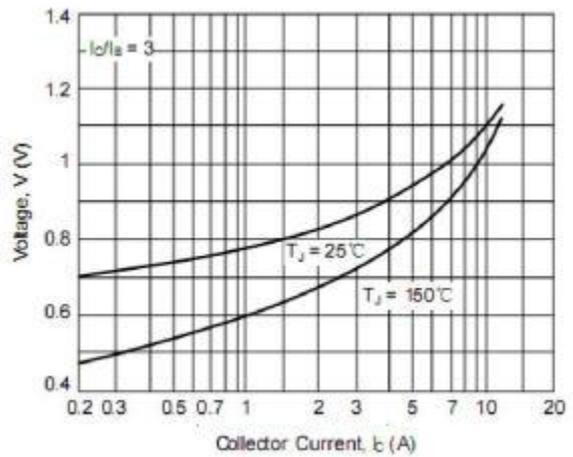


Figure 4. Safe Operating Area Base and

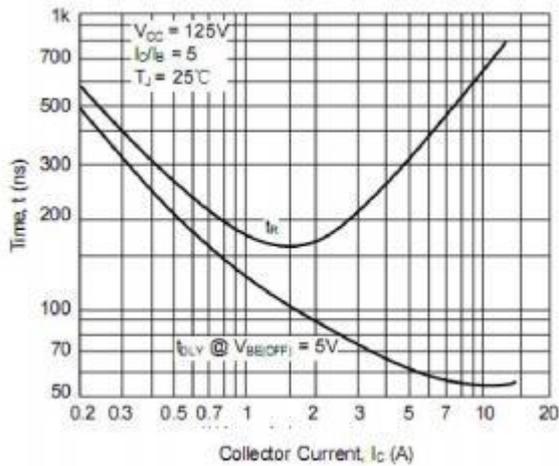


Figure 5. Turn-On Time

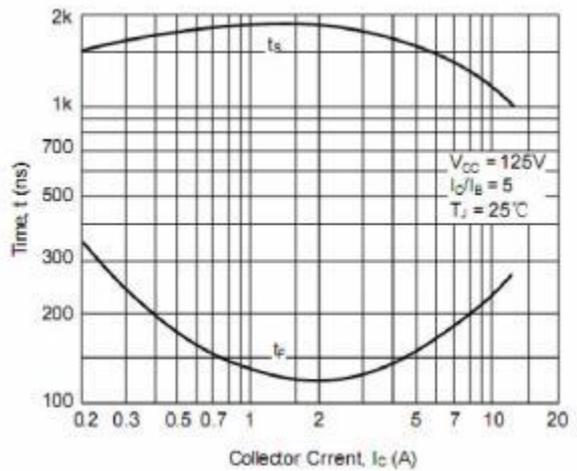
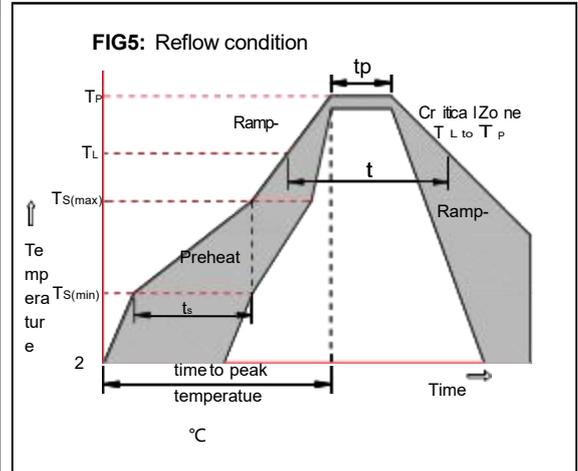


Figure 6. Turn-Off Time

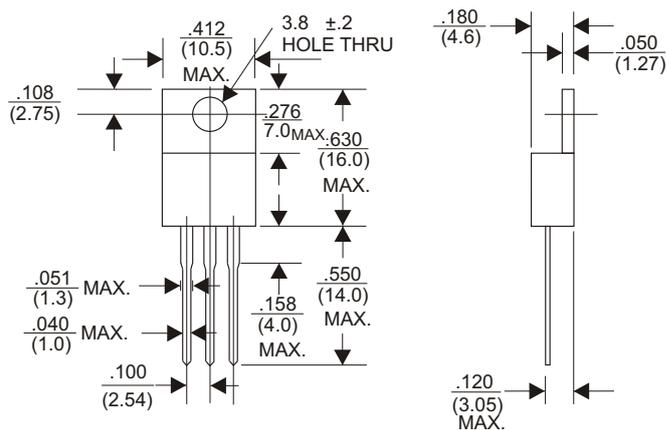
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max ($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature (T_L) (Liquid us)	+217 °C
	-Temperature (t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C



Package Dimensions & Suggested Pad Layout

TO-220



Dimensions in inches and (millimeters)